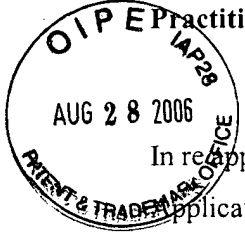


ATF ZMW



Practitioner's Docket No. 51048-2 DIV-RCE

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Goela et al.

Application No.: 09/870,242

Group No.: 1772

Filed: May 30, 2001

Examiner: Walter Aughenbaugh

For: METHOD AND APPARATUS FOR PRODUCING FREE-STANDING  
SILICON CARBIDE ARTICLES

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

CERTIFICATE OF MAILING UNDER 37 C.F.R. SECTION 1.8(a)

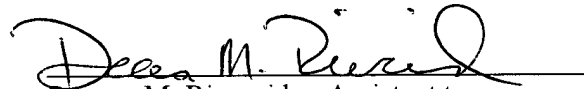
I hereby certify that the attached correspondence comprising:

- (1) Paper Under MPEP §1205.03 (B) In Response to Notification of Non-Compliant Appeal Brief (37 CFR 41.37©(1)(v) (in triplicate); and
- (2) Summary of the Claim Subject Matter (in triplicate).

are being deposited with the United States Postal Service, with sufficient postage, as first class mail in an envelope addressed to:

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Dated: 8/22/2006

  
Deanna M. Rivernider, Assistant to:  
John J. Piskorksi (Reg. No. 35,647)  
Rohm and Haas Electronic Material LLC  
455 Forest Street  
Marlborough, MA 01752  
Telephone: 508-229-7662



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

1048-2 DIV

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: Examiner: Walter  
Aughenbaugh

PAPER UNDER MPEP §1205.03 (B) IN RESPONSE TO NOTIFICATION OF NON-  
COMPLIANT APPEAL BRIEF (37 CFR 41.37(c)(1)(v))

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

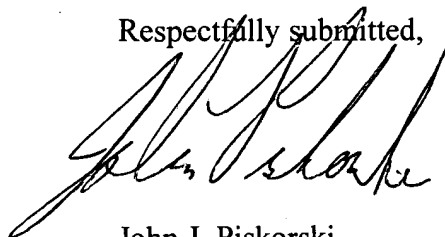
In response to the Notification of Non-Compliant Appeal Brief (37 CFR 41.37) mailed July 28, 2006, Appellant is providing a summary of the claimed subject matter (attached hereto) as required by 37 CFR 41.37(c)(1)(v).

## **V. SUMMARY OF THE CLAIMED SUBJECT MATTER**

Appellant's invention is directed to hollow chemical vapor deposited monolithic silicon carbide shells having an external perimeter of 50 inches or greater and an aspect ratio of 50 or greater (Claim 27 and specification at page 3, lines 9-12, and page 14, lines 19-23). Appellant's invention also is directed to a hollow chemical vapor deposited monolithic silicon carbide shell having an external perimeter of 50 inches or greater, an aspect ratio of 50 or greater and without propagating cracks (Claim 37, and specification at page 3, lines 9-12, page 4, lines 20-25 and lines 29-33 and page 14, lines 19-23).

Appellant's invention also is directed to a hollow chemical vapor deposited monolithic silicon carbide shell (Claim 35, page 1, lines 15-21 and page 3, lines 9-12) made according to a process comprising providing a silicon carbide precursor gas (Claim 35, page 2, lines 24-27, page 3, lines 1-4 and page 12, lines 24-30) in proximity to a surface of a solid substrate or mandrel 42 (Claim 35, page 2, lines 24-26, page 3, lines 4-6, page 7, line 33 to page 8, line 2, Figure 1, Figure 2 and Figure 3) and an isolation device 50 adjacent the solid substrate 42 on a rotating platform 28 in a deposition chamber 16 (Claim 35, page 6, lines 30-32, page 7, lines 24-27, Figure 1, Figure 2 and Figure 3) the solid substrate 42 and the isolation device 50 are separated by a boundary zone 60 (Claim 35, page 8, lines 26-30, Figure 2 and Figure 3); rotating the rotating platform 28 with the solid substrate 42 and isolation device 50 (Claim 35, page 6, line 30 to page 7, line 6 and lines 24-25); reacting silicon carbide precursor gas during rotation to provide a silicon carbide deposit 57 on the surface of the substrate 42 and on the isolation device such that the silicon carbide deposit does not bridge the boundary zone 60 between the solid and the isolation device (Claim 35, page 6, line 30 to page 7, line 11, and page 8, lines 26-32, Figure 2); and removing the silicon carbide deposit to provide a hollow chemical vapor deposited monolithic silicon carbide shell without propagating cracks having an external perimeter of 50 inches or greater and an aspect ratio of 50 or greater (Claim 35, page 4, lines 23-29, page 8, line 32 to page 9, line 3, and page 14, lines 19-23).

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'John J. Piskorski', written in a cursive style.

John J. Piskorski  
Attorney for Applicant  
Registration No. 35,647

Rohm and Haas Electronic Materials, L.L.C.  
455 Forrest Street  
Marlborough, MA 01752  
Telephone No.: (508) 229-7662  
Facsimile No.: (508) 229-0254